

UNISONIC TECHNOLOGIES CO., LTD

UT4421 Power MOSFET

-6.2A, -60V P-CHANNEL POWER MOSFET

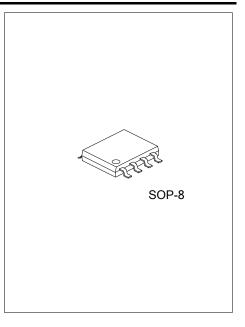
■ DESCRIPTION

The UTC **UT4421** is a P-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance and high switching speed.

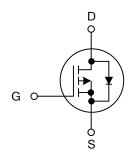
The UTC **UT4421** is suitable for load switch and battery protection applications.



- * $R_{DS(ON)}$ < 40m Ω @ V_{GS} = -10V, I_D = -6.2A $R_{DS(ON)}$ < 50m Ω @ V_{GS} = -4.5V, I_D = -5A
- * High switching speed



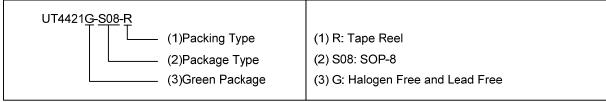
■ SYMBOL



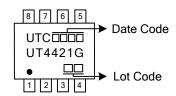
■ ORDERING INFORMATION

Ordering Number	Dookogo	Pin Assignment							Dealine	
	Package	1	2	3	4	5	6	7	8	Packing
UT4421G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



<u>www.unisonic.com.tw</u> 1 of 5

UT4421

■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ extsf{DSS}}$	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous T _A =25°C		-6.2	Α
	(Note 1) T _A =70°C	I _D	-5	Α
	Pulsed (Note 2)	I _{DM}	-40	Α
Power Dissipation (Note 1)		P_{D}	2	W
Junction Temperature		TJ	-55~+150	°C
Storage Temperature Range		T_{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	75	°C/W
Junction to Case	θ_{JC}	30	°C/W

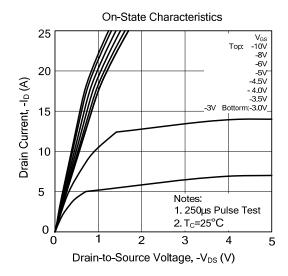
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

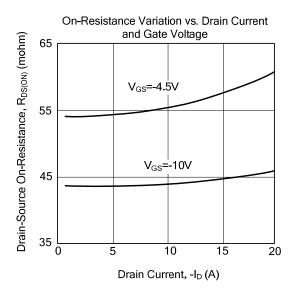
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =-250μA, V _{GS} =0V	-60			V
Zoro Cata Voltago Drain Current	I _{DSS}	V_{DS} =-48V, V_{GS} =0V			-1	μΑ
Zero Gate Voltage Drain Current		V _{DS} =-48V, V _{GS} =0V, T _J =55°C			-5	μΑ
Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nΑ
Gate-Source Leakage Current Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1	-2	-3	V
On State Drain Current	I _{D(ON)}	V _{GS} =-10V, V _{DS} =-5V	-40			Α
Olutio Burin Our and Our Olute Burintana	R _{DS(ON)}	V _{GS} =-10V, I _D =-6.2A		43	48	mΩ
Static Drain-Source On-State Resistance		V _{GS} =-4.5V, I _D =-5A		58	63	mΩ
Forward Transconductance	g fs	V _{DS} =-5V, I _D =-6.2A		18		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}			2417	2900	pF
Output Capacitance	Coss	V _{GS} =0V, V _{DS} =-30V, f=1.0MHz		179		pF
Reverse Transfer Capacitance	C _{RSS}			120		pF
Gate Resistance	R_G	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.9	2.3	Ω
SWITCHING PARAMETERS			•	•		
Total Gate Charge	Q_{G}	V _{GS} =-4.5V, V _{DS} =-30V, I _D =-6.2A		22.7		nC
Total Gate Charge	Q_{G}			46.5	55	nC
Gate to Source Charge	Q_GS	V _{GS} =-10V, V _{DS} =-30V, I _D =-6.2A		9.1		nC
Gate to Drain Charge	Q_{GD}			9.2		nC
Turn-ON Delay Time	t _{D(ON)}			9.8		ns
Rise Time	t _R	V_{GS} =-10V, V_{DS} =-30V, R_L =4.7 Ω ,		6.1		ns
Turn-OFF Delay Time	t _{D(OFF)}	R _{GEN} =3Ω		44		ns
Fall-Time	t _F	1		12.7		ns
SOURCE- DRAIN DIODE RATINGS AND	CHARACTER	RISTICS	•	•		
Maximum Body-Diode Continuous					4.0	
Current	Is				-4.2	Α
Diode Forward Voltage	V_{SD}	I _S =-1A,V _{GS} =0V		-0.74	-1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F =-6.2A, dI/dt=100A/μS		34	42	ns
Body Diode Reverse Recovery Charge	Q _{rr}			47		nC
Notes: 1 The value of A is measured w		255 Alband 111 6	. 			

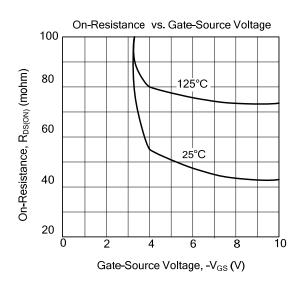
Notes: 1. The value of θ_{JA} is measured with the device mounted on 1in²FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤10s thermal resistance rating.

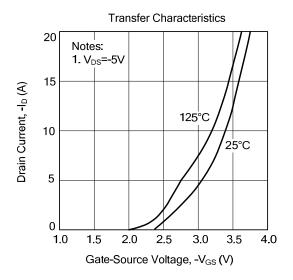
- 2. Repetitive rating, pulse width limited by junction temperature.
- 3. The θ_{JA} is the sum of the thermal impedence from junction to lead θ_{JL} and lead to ambient.

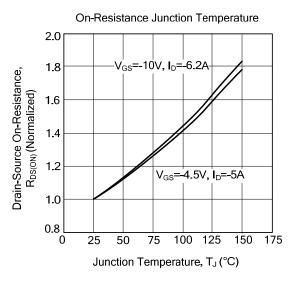
■ TYPICAL CHARACTERISTICS

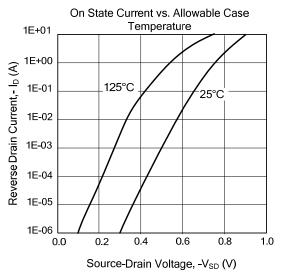




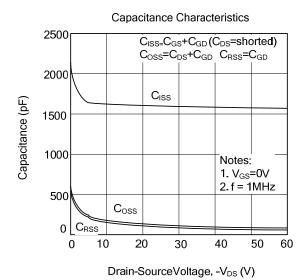


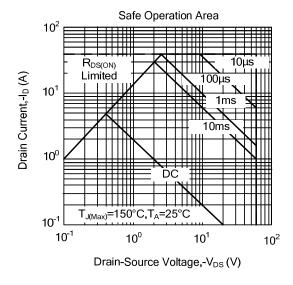






■ TYPICAL CHARACTERISTICS (Cont.)





UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Unisonic manufacturer:

Other Similar products are found below:

614233C 648584F FDPF9N50NZ IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2267(Q) 2SK2545(Q,T)

405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C PSMN4R2-30MLD

TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B

IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IPS60R1K0PFD7SAKMA1 IPS60R360PFD7SAKMA1

IPS60R600PFD7SAKMA1 IPS60R210PFD7SAKMA1 DMN2990UFB-7B